



DMG7N65SCT

Product Summary

BV _{DSS}	Rds(on)	Ι _D T _C = +25°C	
650V	1.4Ω@V _{GS} = 10V	7.7A	

N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low Input Capacitance
 - High BVDSS Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

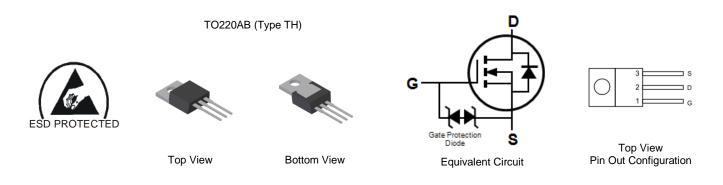
Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMG7N65SCT	TO220AB (Type TH)	50 Pieces/Tube

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	650	V
Gate-Source Voltage			V _{GSS}	±30	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T _C = +25°C T _C = +100°C	ID	7.7 4.8	А
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	lD	1.1	А
Maximum Body Diode Forward Current (Note 5)			ls	7.7	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			Idм	10	А
Avalanche Current, L = 60mH (Note 6)			las	1.1	А
Avalanche Energy, L = 60mH (Note 6)			Eas	42	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Tc = +25°C	D -	125	W
Total Power Dissipation (Note 5)	Tc = +100°C	PD	50	vv
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{0JA}	50	°C/W
Thermal Resistance, Junction to Case (Note 5)		Rejc	1	C/VV
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

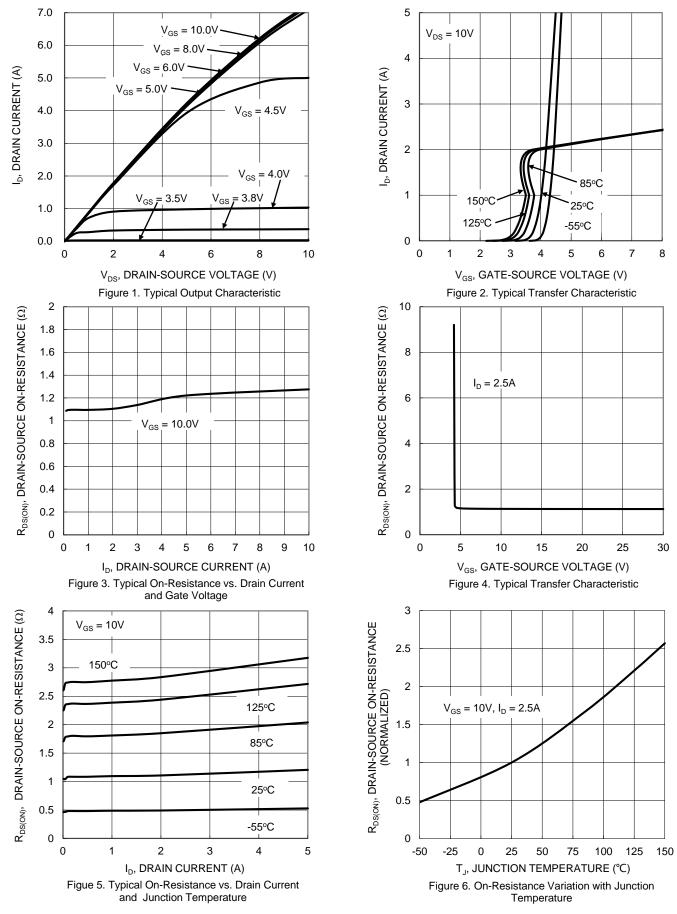
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	CJ2C		• 76		•••••		
Drain-Source Breakdown Voltage	BVDSS	650	_		V	Vgs = 0V, Ip = 250µA	
Zero Gate Voltage Drain Current	IDSS	-	_	1	μA	V _{DS} = 650V, V _{GS} = 0V	
Gate-Source Leakage	lgss	-	_	10	μA	$V_{GS} = \pm 24V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2	3	4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)		1.1	1.4	Ω	VGS = 10V, ID = 2.5A	
Diode Forward Voltage	Vsd		0.8	1.5	V	$V_{GS} = 0V$, $I_S = 5A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	Ciss		886	_			
Output Capacitance	Coss		63	_	pF	V _{DS} = 50V, f = 1.0MHz, V _{GS} = 0	
Reverse Transfer Capacitance	Crss		8.9	_			
Gate Resistance	Rg	_	1.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	25.2	_		\/ 100\/ L 5A	
Gate-Source Charge	Qgs	_	3.5	_	nC	V _{DS} = 480V, I _D = 5A, V _{GS} = 10V	
Gate-Drain Charge	Q _{gd}	_	12.4	_			
Turn-On Delay Time	td(on)	_	10	_			
Turn-On Rise Time	t _R	_	11	_	ns	$\label{eq:VDS} \begin{split} V_{DS} &= 300 V, R_G = 4.7 \Omega, I_D = 2.5 A, \\ V_{GS} &= 10 V \end{split}$	
Turn-Off Delay Time	tD(OFF)	_	36	_	115		
Turn-Off Fall Time	t⊢		15]		
Body Diode Reverse Recovery Time	t _{RR}	_	271	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	1908		μC	$V_{DS} = 60V, I_F = 5A, dI/dt = 100A/\mu s$	

Notes: 5. Device mounted on an infinite heatsink.

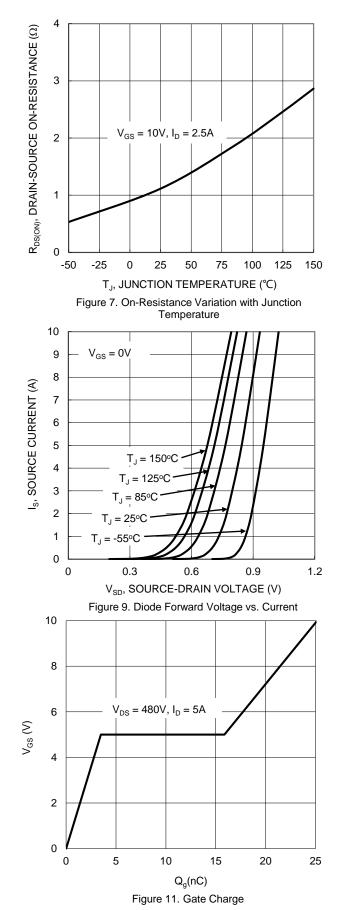
Guaranteed by design. Not subject to production testing.
Short duration pulse test used to minimize self-heating effect.

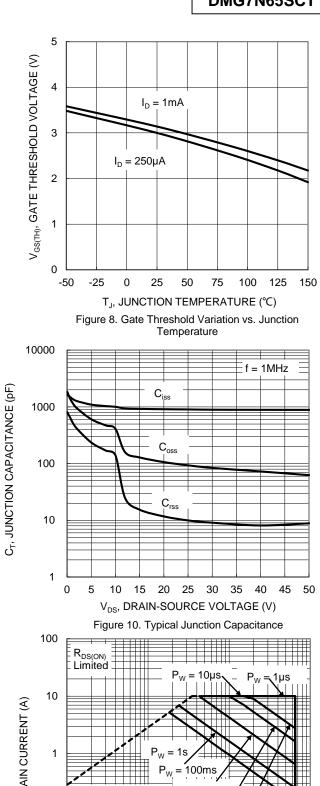


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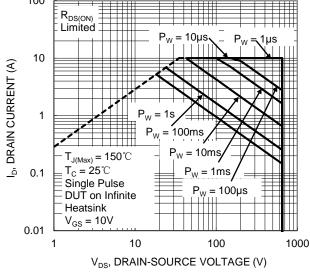
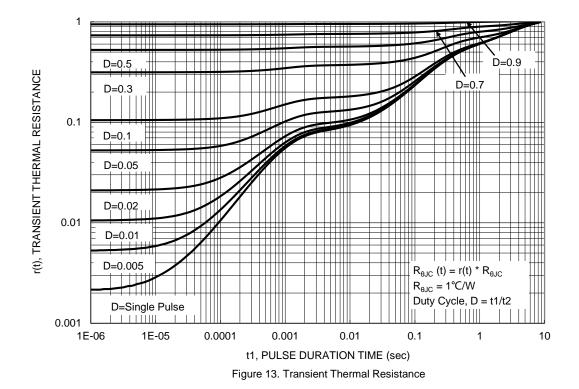


Figure 12. SOA, Safe Operation Area

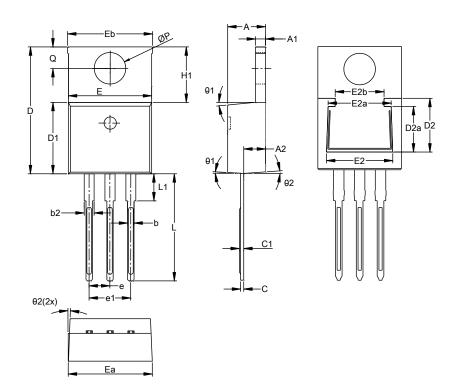






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



TO220AB (Type TH)	TO220AB	(Type	TH)
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TO220AB (Type TH)					
Dim	Min	Max	Тур		
Α	4.27	4.87	4.57		
A1	1.12	1.42	1.27		
A2	2.39	2.99	2.69		
b	0.70	1.01	0.81		
b2	1.17	1.50	1.27		
С	0.30	0.53	0.38		
c1	0.38	0.72	0.56		
D	14.60	15.40	15.00		
D1	8.40	9.00	8.70		
D2	5.33	6.63	6.33		
D2a	4.54	5.84	5.54		
е	2.54 BSC				
e1		5.08 BSC	;		
E	9.88	10.50	10.16		
Ea	9.90	10.45	10.10		
Eb	9.90	10.65	10.25		
E2	7.06	8.36	8.06		
E2a	6.67	7.97	7.67		
E2b	4.94	6.24	5.94		
H1	5.70	6.65	6.30		
L	13.00	13.80	13.40		
L1	-	4.10	3.75		
Q	2.50	2.99	2.74		
ØP	3.70	3.99	3.84		
θ1	4°	10°	7°		
θ2	0°	6°	3°		
All	All Dimensions in mm				



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